

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Gab-jin Nam et al;  
Serial No.: to be assigned  
Filed: concurrently herewith  
For: METHODS OF FORMING ELECTRONIC DEVICES INCLUDING  
DIELECTRIC LAYERS WITH DIFFERENT DENSITIES OF TITANIUM AND  
RELATED STRUCTURES

July 9, 2002

Mail Stop Patent Application  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**PRELIMINARY AMENDMENT**

Sir:

Prior to examination of this application, please amend the above-identified application as indicated below. Attached hereto is a marked up version of the changes made to the claims by the current amendment. The marked up version of the changes is captioned "**Version With Markings To Show Changes Made**". Entry of this Preliminary Amendment and allowance of the present application are respectfully requested in due course.

**In the Claims:**

Please cancel Claims 15-26, 41-52, 54-57, 64-77, and 79-91.

Please amend Claim 53 as indicated below.

53.(Amended) A semiconductor memory device comprising:

a semiconductor substrate;

a lower electrode formed on the semiconductor substrate;

a dielectric layer which is an oxide film including titanium and tantalum, on an

upper surface of the lower electrode; and

an upper electrode on an upper surface of the dielectric layer,

wherein the density of titanium in the dielectric layer depends on the thickness of the dielectric layer;